

Title (en)

DOPED SEMICONDUCTOR NANOCRYSTALS, METHOD FOR PREPARING SAME AND USES THEREOF

Title (de)

DOTIERTE HALBLEITERNANOKRISTALLE, VERFAHREN ZUR HERSTELLUNG DAVON UND VERWENDUNGEN DAVON

Title (fr)

NANOCRISTAUX DE SEMI-CONDUCTEURS DOPÉS, LEUR PROCÉDÉ DE PRÉPARATION ET LEURS UTILISATIONS

Publication

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Application

**EP 19850730 A 20191223**

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Abstract (en)

[origin: WO2020136347A1] The present invention concerns a set of nanocrystals comprising a semiconductor comprising A representing a metal or metalloid in the +III oxidation state and B representing an element in the -III oxidation state, the nanocrystals being doped, on average per nanocrystal, by an atom of C chosen from the transition metals in the +I or +II oxidation state. The present invention also relates to the method for preparing same and to the various uses thereof.

IPC 8 full level

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